FORM PTO-14 Rev. 2-82)		ART. OF COMM AND TRADEMAI	ATTY. DOCKET NO. 00-103		SERIAL NO. 09/731,596			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)			APPLICANT Margaret S. Fyfield					
			FILING DATE December 6, 2000		GROUP 2813			
	MIL	U.S.	. PATENT	DOCUMENTS				
EXAM. INIT.	_	DEMARK ON THE NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILIN DATE APPR PRIAT	IF O-
						L	<u> </u>	
7.1		FORE	GN PATEN	T DOCUMENTS		,		
	DOCUMENT NUMBER DATE			COUNTRY	CLASS	SUB-	TRANS- LATION	
	T-1 T-					CLASS	YES	NO
						L		
01	THER DOCL	IMENTS (Inclu	uding Auth	or, Title, Date, Pe	rtinent Pa	ges, Etc.)	
4/2	Gary Shade and Kendaß Scott Wills, Photoemission Microscopy, 1997 ASM International, pp. 181-182.							
y/8	B. Bossmann, P. Baurachmidt, K. Hussey, and E. Black, Feiture Analysis Techniques with the Confocal Leser Scenning Microscope, ISTFA '92: The 18th International Symposium for Testing & Faiture Analysis, October 1992, pp. 351-361							
	Nevil M. Wu, Kevin Weaver, James H. Lin, Failure Analysis from Back Side of Die, ISTFA '96: 22 rd International Syr Testing and Failure Analysis, November 1996, 7 pages							n for
	TW. Joseph,	A.L. Berry, B. Bossma Symposium for Testing	n, <i>Infrared Laser</i> & Failure Analys	Microscopy of Structures on is, October 1992, pp. 1-7	Heavily Doped	Silicon, ISTFA	'92: The 1	8 ^{ca}
	D.L. Barton, P. Tangyunyong, J.M. Soden, A.Y. Liang, F.J. Low, A.N. Zapiztin, K. Shivanandan, and G. Donohoe, Infrared Light Emission from Semiconductor Devices, Proceedings of the 22 nd International Symposium for Testing and Faiture Analysis, November 1996, pp. 9-17							
	Chun-Cheng		and Kurt Hurley,	Backside waveform probing	of CMOS device	s using infrare	d laser at	
	C. Chiang, N. Khurana, D.T. Hurley, and K. Teasdale, Backside Emission Microscopy for Integrated Circuits on Heavily Doped Substrate, Proceedings from the 24th International Symposium for Testing and Failure Analysis, November 1998, pp. 447-453							
	Kandali Scott Wills, Terril Lewis, Greg Billus, Hai Hoang, Optical Beam Induced Current Applications for Fallure Analyst Devices, 1997 ASM International, pp. 21-26							
111	Yeoh Eng Hong and Martin Tay Tiong We, The application of novel Fallure Analysis Techniques for Advanced Multi-Layered CMOS devices, 6 pages							
	T. Koyama, Y. Mashiko, M. Sekine, H. Koyama and K. Horie, New non-bias optical beam induced current (NB-OBIC) techniques for evaluation of A1 interconnects, 1995 IEEE, pp. 228-233							
	Said F. Al-sara March 1997, p		Bonding, Centre f	or High Performance Integral	ed Technologies	and Systems	(CHIPTEC	;).
m	Said F. Al-sara 1997, 1 page	rwi, Solder Bump Bond	ting, Centre for H	igh Performance Integrated	l'echnologies an	d Systems (CH	IPTEC), N	larch
XAMINER	(L. O. M	A DATE C	ONSIDERED	· · · · · · · · · · · · · · · · · · ·	0/10	05		

Best Available Copy